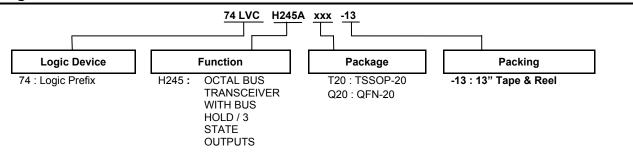


Ordering Information



Part Number	Package	Package	Package	13" Tape	and Reel
Part Number	Code	(Note 4 & 5)	Size	Quantity	Part Number Suffix
74LVCH245AT20-13	T20	TSSOP-20	6.4mm X 6.5mm X 1.2mm 0.65 mm lead pitch	2500/Tape & Reel	-13
74LVCH245AQ20-13	Q20	V-QFN4525-20	2.5mm X 4.5mm X 0.95mm 0.50 mm lead pitch	2500/Tape & Reel	-13

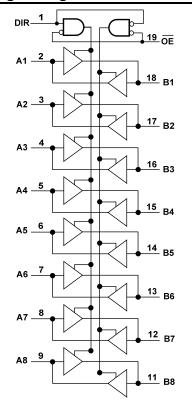
Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. V-QFN4525-20 is a JEDEC recognized naming convention that specifies the package thickness category as V and the number 4525 describes the package as 4.5mm X 2.5mm.

Pin Descriptions

Pin	Pin	Description
Number	Name	Description
1	DIR	Direction Control
2	1A1	Data Input
3	2Y4	Data Output
4	1A2	Data Input
5	2Y3	Data Output
6	1A3	Data Input
7	2Y2	Data Output
8	1A4	Data Input
9	2Y1	Data Output
10	GND	Ground
11	2A1	Data Input
12	1Y4	Data Output
13	2A2	Data Input
14	1Y3	Data Output
15	2A3	Data Input
16	1Y2	Data Output
17	2A4	Data Input
18	1Y1	Data Output
19	20E	Output Enable 2
20	Vcc	Supply Voltage

Logic Diagram



Function Table

INP	UTS	•	
ŌE	DIR	Operation	
L	L	B Data to A Bus	
L	Н	A Data to B Bus	
Н	Х	Bus Isolation	



Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
Vcc	Supply Voltage Range	-0.5 to +7.0	V
VI	Input Voltage Range	-0.5 to +7.0	V
I _{IK}	Input Clamp Current VI< 0V	-20	mA
I _{OK}	Output Clamp Current V _O < 0V	-50	mA
lo	Continuous Output Current -0.5V < V _O V _{CC} +0.5V	±50	mA
lcc	Continuous Current Through V _{CC}	100	mA
I _{GND}	Continuous Current Through GND	-100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C
P _{TOT}	Total Power Dissipation	500	mW

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
	Operating	1.65	3.6	V	
V _{CC}	Supply Voltage	Data Retention Only	1.5	_	V
VI	Input Voltage	—	0	5.5	V
Vo	Output Voltage	—	0	V _{CC}	V
		V _{CC} = 1.65V	—	-4	
	High-Level Output Current	V _{CC} = 2.3V	—	-8	
Юн		V _{CC} = 2.7V	—	-12	mA
		V _{CC} = 3.0V	—	-24	
		V _{CC} = 1.65V	—	4	
		V _{CC} = 2.3V	—	8	6
IOL	Low-Level Output Current	V _{CC} = 2.7V	—	12	mA
		V _{CC} = 3.0V	—	24	
Δt/ΔV	Input Transition Rise or Fall Rate		—	10	ns/V
T _A	Operating Free-Air Temperature		-40	+125	°C



Electrical Characteristics

Ourseland	Demonster	Toot Conditions		T _A = -40°C	C to +85°C	T _A = -40°C	to +125°C	11
Symbol	Parameter	Test Conditions	V _{cc}	Min	Max	Min	Max	Unit
			1.65V to 1.95	V _{CC} X 0.65		V _{CC} X 0.65	_	
V _{IH}	High-Level Input Voltage		2.3V to 2.7V	1.7		1.7		V
	vollage		3.0V to 3.6 V	2		2	_	
			1.65V to 1.95	_	V _{cc} X 0.35	_	V _{cc} X 0.35	
VIL	Low-Level input voltage		2.3V to 2.7V	_	0.7	_	0.7	V
	voltage		3.0 V to 3.6V	_	0.8	_	0.8	
		I _{он} = -50µА	1.65V to 5.5V	V _{CC} -0.2	—	V _{CC} -0.3	—	
		I _{он} = -4mА	1.65V	1.2	—	1.05	—	
V	High-Level Output	I _{он} = -8mA	2.3V	1.7	—	1.65	—	
V_{OH}	Voltage	L = 10mA	2.7V	2.2	—	2.05	—	v
		I _{он} = -12mA	3.V	2.4	—	2.48	—	v
		I _{OH} = -24mA	3.0V	2.3	—	2.0	—	
		I _{OL} = 100μA	1.65V to 5.5V	—	0.2	—	0.3	
		I _{OL} = 4mA	1.65V	—	0.45	—	0.65	
V _{OL}	Low-Level Output Voltage	I _{OL} = 8mA	2.3V	—	0.60	_	0.80	V
		I _{OL} = 12mA	2.7V	_	0.40	_	0.60	
		I _{OL} = 24mA	3.V	—	0.55	—	0.80	
I _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 0$ or 5.5V	0V	_	±10	—	±20	μA
I,	Input Current Control Pins	V _I = GND or 5.5V	0 to 5.5V	_	±5	_	±20	μA
		V _I = 0.58V		25		15		
		V _I = 1.07	1.65V	-25	_	-15	_	
	Input Current	V ₁ = 0.7V	2.3V	45	_	35	_	
I _{I(HOLD)}	Required to Change	V _I = 1.7V	2.3V	-45	_	-35	—	μA
	State	V ₁ = 0.8V	2.0\/	75	—	60	—	
		V ₁ = 2.0V	3.0V	-75	—	-60	—	
		V _I = 0 or 3.6V	3.6V	—	±500	—	±500	
I _{oz}	Z-State current	V ₁ = GND or 5.5V V ₀ = 0 or 5.5V	3.6V	—	±5	—	± 20	uA
Icc	Supply Current	$V_{I} = GND \text{ or } V_{CC}$ $I_{O} = 0$	6.0V	_	10	—	40	μA
ΔI_{CC}	Additional Supply Current	One input at V _{CC} -0.6V lo = 0A	2.7V to 3.6V	_	500	_	5000	μA
Ci	Input Capacitance	V_{I} = GND or V_{CC}	3.3V	4.0 ty	/pical	4.0 ty	pical	
Co	Output Capacitance	V_{o} = GND or V_{cc}	3.3V	5.5 ty	/pical	5.5 typical		pF



Switching Characteristics

Symbol Parameter	Test Conditions	V _{cc}	-	Γ _A = +25°0	•		l0°C to 5°C		0°C to 5°C	Unit			
		Conditions		Min	Ту	Max	Min	Max	Min	Max			
	_		1.8V ± 0.15V	1	6.0	12.2	1	12.7	1	16.9			
	Propagation	Figure 1	2.5V ± 0.2V	1	3.9	8.1	1	8.5	1	9.1			
t _{PD}	Delay A _N to B _N or B _N to A _N		2.7V	1	4.2	8.7	1	9.6	1	9.9	ns		
			3.3V ± 0.3V	1.5	3.8	8.1	1.5	8.7	1.5	9.2			
	Enable Time \overline{OE} to A _N		Enable Time		1.8V ± 0.15V	1	7	14.8	1	15.3	1	22.5	
			Figure 1	2.5V ± 0.2V	1	4.5	10	1	10.5	1	12.4		
t _{EN}		-	2.7V	1	5.4	9.3	1	9.5	1	12.0	ns		
	or \overline{OE} to B_N		3.3V ± 0.3V	1.5	4.4	8.3	1.5	8.5	1.5	11.0			
	Disable Time		1.8V ± 0.15V	1	7.8	16.5	1	17	1	18.4			
	\overline{OE} to A _N	Figure 1	2.5V ± 0.2V	1	4	9	1	9.5	1	10.5			
tDIS	$\begin{array}{c} \text{TDIS} & \text{OE to } A_{N} \\ \text{or } \overline{\text{OE}} \text{ to } B_{N} \end{array}$	-	2.7V	1	4.4	8.3	1	8.5	1	10.0	ns		
			3.3V ± 0.3V	1.7	4.1	7.3	1.7	7.5	1.7	9.0			
t _{sk(0)}	Output Skew Time		3.3V ± 0.3V	_	_	1.0	_	_	_	1.5	ns		

Operating Characteristics

T _A = +25°C					
Symbol	Parameter	Test Conditions	Vcc	Тур	Unit
	Deven die ein etien		1.8V ± 0.15V	9.9	
C _{pd}	Power dissipation capacitance per gate	F = 10MHz Outputs Enabled	2.5V ± 0.2V	10.2	pF
	capacitance per gate		3.3V ± 0.3V	10.6	

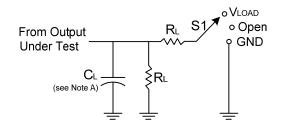
Package Characteristics

Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
θ _{JA}	Thermal Resistance Junction-to-Ambient	TSSOP-20	(Note 8)	_	74	_	°C/W
θ _{JC}	Thermal Resistance Junction-to-Case	TSSOP-20	(Note 8)	_	15	_	°C/W
θ _{JA}	Thermal Resistance Junction-to-Ambient	V-QFN4525-20	(Note 8)	_	67	_	°C/W
θ _{JC}	Thermal Resistance Junction-to-Case	V-QFN4525-20	(Note 8)	_	20	_	°C/W

Note: 8. Test conditions for TSSOP-20 and V-QFN4525-20: Devices mounted on 4 layer FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout per JESD 51-7.



Parameter Measurement Information

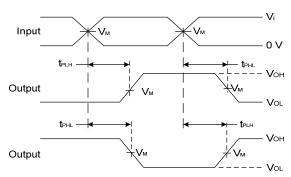


TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	VLOAD
t _{PHZ} /t _{PZH}	GND

	In	puts	N.			-	V۵
V _{cc}	VI	t _r /t _f	V _M V _{LOAD}		C∟	C _L R _L	
1.8V ± 0.15V	V _{CC}	≤2ns	V _{CC} /2	$2 \times V_{CC}$	30pF	1KΩ	0.15V
2.5V ± 0.2V	Vcc	≤2ns	V _{CC} /2	2 x V _{CC}	30pF	500Ω	0.15V
2.7V	2.7V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V
3.3V ± 0.3V	2.7V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V



Voltage Waveform Pulse Duration

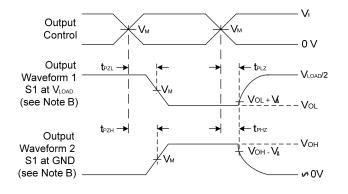




- Notes: A. Includes test lead and test apparatus capacitance. B. All pulses are supplied at pulse repetition rate \leq 10 MHz. C. Inputs are measured separately one transition per measurement. D. t_{PLZ} and t_{PHZ} are the same as t_{dis.} E. t_{PZL} and t_{PZH} are the same as t_{EN0}

 - F. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$

Figure 1 Load Circuit and Voltage Waveforms

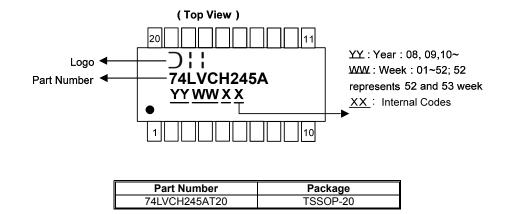


Voltage Waveform Enable and Disable Times Low and High Level Enabling

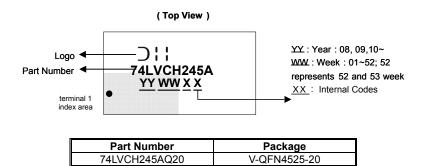


Marking Information

(1) TSSOP20



(2) QFN-20 (V-QFN4525-20)

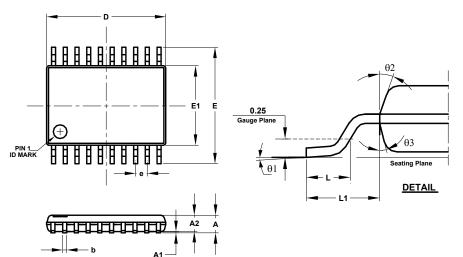




Package Outline Dimensions (All Dimensions in mm)

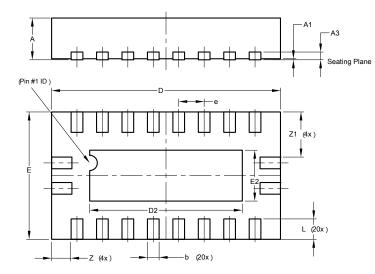
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

(1) TSSOP-20



	TSSO	P-20				
Dim	Min Max Typ					
Α	-	1.20	-			
A1	0.05	0.15	-			
A2	0.80	1.05	-			
b	0.19	0.30	-			
С	0.09	0.20	-			
D	6.40	6.60	6.50			
Е	6.20	6.60	6.40			
E1	4.30	4.50	4.40			
е	0	.65 BSC)			
L	0.45	0.75	0.60			
L1		1.0 REF				
θ1	0°	8°	-			
θ2	10°	14°	12°			
θ3	10°	14°	12°			
All I	Dimensi	ons in r	nm			

(2) QFN-20 (V-QFN4525-20)



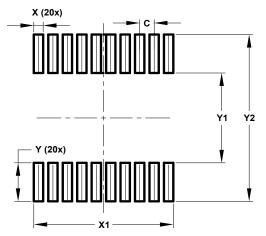
V-QFN4525-20				
Dim	Min	Max	Тур	
Α	0.75	0.85	0.80	
A1	0.00	0.05	0.02	
A3	-	-	0.15	
b	0.18	0.30	0.23	
D	4.45	4.55	4.50	
D2	2.85	3.15	3.00	
ш	2.45	2.55	2.50	
E2	0.85	1.15	1.00	
е	0.50BSC			
L	0.30	0.50	0.40	
Z	-	-	0.385	
Z1	-	-	0.885	
All Dimensions in mm				



Suggested Pad Layout

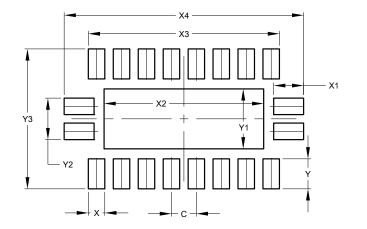
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(1) TSSOP-20



Dimensions	Value (in mm)	
С	0.650	
Х	0.420	
X1	6.270	
Y	1.789	
Y1	4.160	
Y2	7.720	

(2) QFN-20 (V-QFN4525-20)



Dimensions	Value (in mm)
С	0.500
Х	0.330
X1	0.600
X2	3.200
X3	3.830
X4	4.800
Y	0.600
Y1	1.200
Y2	0.830
Y3	2.800



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